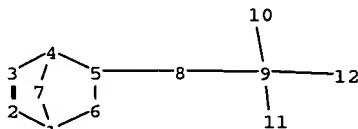
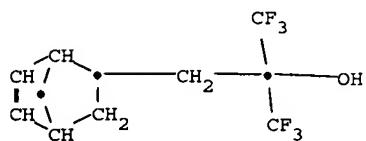
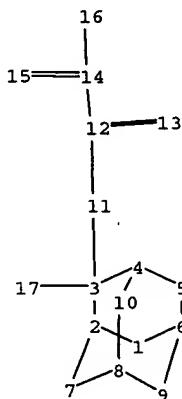
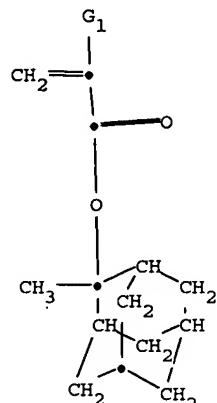


- 10/719, 905, 8/16/05  
maleic anhydride in (P)  
108-31-6 / CRN

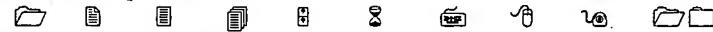
SEARCH: CA Reg. File  
STRUCTure search. Polymers  
in claim 4.

All have  $\text{Nb}^{+}$  + molar Anions.





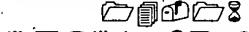
မြန်မာစာ မြေးယူမှု



四庫全書



□❖■❖❖ ❁□■❖❖ •



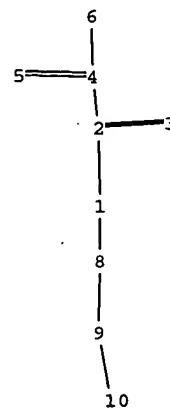
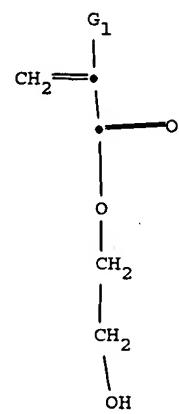
ମୁଦ୍ରଣ କାର୍ଯ୍ୟଶାଖା • ପିଲାମାନାର ପିଲାମାନା



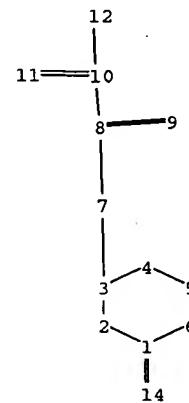
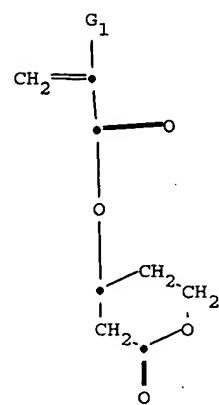
A row of small, light-colored icons used for navigating through files or applications. From left to right, they include: a document with a checkmark, a folder, a laptop, a tree, a mail icon, a speech bubble, a person icon, and a bar chart.



ଶାନ୍ତିରେ ପାଦମଣିକୁ ଏହାରେ ଆଜିମାତ୍ରା କିମ୍ବା ଏହାରେ ଆଜିମାତ୍ରା



ପାଦମଣିକୁ ଏହାରେ ଆଜିମାତ୍ରା



ପ୍ରକାଶକ ମାନ୍ୟମାତ୍ରା

ପାଠ୍ୟ ମାନ୍ୟମାତ୍ରା

L30 ANSWER 1 OF 1 CAPLUS COPYRIGHT 2005 ACS on STN

AN 2005:98956 CAPLUS

DN 142:207614

TI Photoresist polymer and photoresist composition containing the same

IN Lee, Geun Su; Bok, Cheol Kyu; Moon, Seung Chan; Shin, Ki Soo; Kim, Jae Hyun; Kim, Jung Woo; Lee, Sang Hyang; Kang, Jae Hyun

PA S. Korea

SO U.S. Pat. Appl. Publ., 17 pp.

CODEN: USXXCO

DT Patent

LA English

FAN CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI US 2005026070	A1	20050203	US 2008-719905	20031121
PRAI KR 2003-52337	A	20030729		

AB Photoresist polymers and photoresist compns. are disclosed. A photoresist polymer is represented by I ( $X_{1-4} = CH_2, CH_2CH_2, S; R_{1,2} = H, CH_3, CF_3; R_3 = C_{1-20}$  alkyl, etc.;  $R_4 = C_{1-20}$  hydroxyalkyl, etc.;  $R_5 = H, C_{1-20}$  hydroxyalkyl, etc.;  $m = 0-2$ ; and  $n = 0, 1$ ). The photoresist compns. have excellent etching resistance, thermal resistance and adhesive property, and high affinity to an developing solution, thereby improving LER (line edge roughness).

IT 836623-60-0P 836623-61-1P

RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)  
(photoresist polymer for photoresist composition)

RN 836623-60-0 CAPLUS

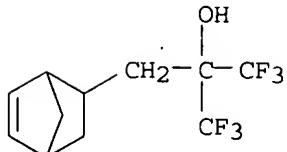
CN 2-Propenoic acid, 2-methyl-, 1,1-dimethylethyl ester, polymer with  $\alpha,\alpha$ -bis(trifluoromethyl)bicyclo[2.2.1]hept-5-ene-2-ethanol, 2,5-furandione and 2-hydroxyethyl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

CM 1

M.J. APP!

CRN 196314-61-1

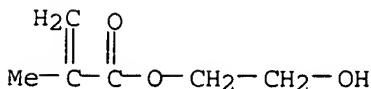
CMF C11 H12 F6 O



CM 2

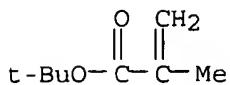
CRN 868-77-9

CMF C6 H10 O3



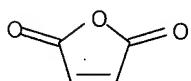
CM 3

CRN 585-07-9  
CMF C8 H14 O2



CM 4

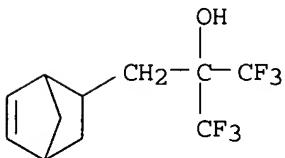
CRN 108-31-6  
CMF C4 H2 O3



RN 836623-61-1 CAPLUS  
CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylethyl ester,  
polymer with  $\alpha,\alpha$ -bis(trifluoromethyl)bicyclo[2.2.1]hept-5-ene-  
2-ethanol, 1,1-dimethylethyl 2-methyl-2-propenoate, 2,5-furandione and  
2-hydroxyethyl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

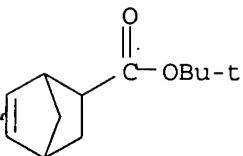
CM 1

CRN 196314-61-1  
CMF C11 H12 F6 O



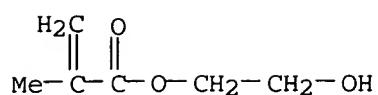
CM 2

CRN 154970-45-3  
CMF C12 H18 O2



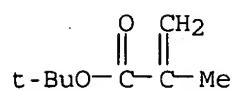
CM 3

CRN 868-77-9  
CMF C6 H10 O3



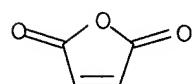
CM 4

CRN 585-07-9  
CMF C8 H14 O2



CM 5

CRN 108-31-6  
CMF C4 H2 O3



=>

L32 ANSWER 1 OF 1 CAPLUS COPYRIGHT 2005 ACS on STN

AN 2005:98956 CAPLUS

DN 142:207614

TI Photoresist polymer and photoresist composition containing the same  
IN Lee, Geun Su; Bok, Cheol Kyu; Moon, Seung Chan; Shin, Ki Soo; Kim, Jae  
Hyun; Kim, Jung Woo; Lee, Sang Hyang; Kang, Jae Hyun

PA S. Korea

SO U.S. Pat. Appl. Publ., 17 pp.

CODEN: USXXCO

DT Patent

LA English

FAN CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI US 2005026070	A1	20050203	US 2003-719905	20031121
PRAI KR 2003-52337	A	20030729		

AB Photoresist polymers and photoresist compns. are disclosed. A photoresist polymer is represented by I ( $X_{1-4} = CH_2, CH_2CH_2, S; R_{1,2} = H, CH_3, CF_3; R_3 = C_{1-20}$  alkyl, etc.;  $R_4 = C_{1-20}$  hydroxyalkyl, etc.;  $R_5 = H, C_{1-20}$  hydroxyalkyl, etc.;  $m = 0-2$ ; and  $n = 0, 1$ ). The photoresist compns. have excellent etching resistance, thermal resistance and adhesive property, and high affinity to an developing solution, thereby improving LER (line edge roughness).

IT 836623-58-6P 836623-59-7P

RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)  
(photoresist polymer for photoresist composition)

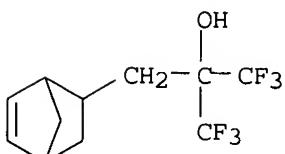
RN 836623-58-6 CAPLUS

CN 2-Propenoic acid, 2-methyl-, 2-hydroxyethyl ester, polymer with  $\alpha,\alpha$ -bis(trifluoromethyl)bicyclo[2.2.1]hept-5-ene-2-ethanol, 2,5-furandione and 2-methyltricyclo[3.3.1.13,7]dec-2-yl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 196314-61-1

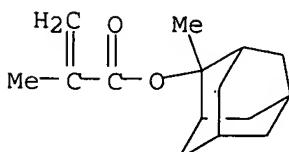
CMF C11 H12 F6 O



CM 2

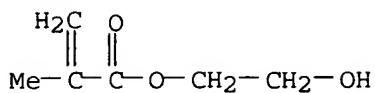
CRN 177080-67-0

CMF C15 H22 O2



CM 3

CRN 868-77-9  
CMF C6 H10 O3



CM 4

CRN 108-31-6  
CMF C4 H2 O3

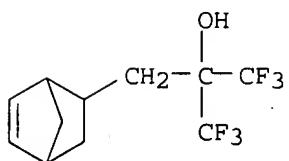


RN 836623-59-7 CAPLUS

CN 2-Propenoic acid, 2-methyl-, 2-hydroxyethyl ester, polymer with  
bicyclo[2.2.1]hept-2-ene,  $\alpha,\alpha$ -bis(trifluoromethyl)bicyclo[2.2.  
1]hept-5-ene-2-ethanol, 2,5-furandione and 2-methyltricyclo[3.3.1.13,7]dec-  
2-yl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

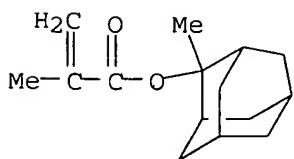
CM 1

CRN 196314-61-1  
CMF C11 H12 F6 O



CM 2

CRN 177080-67-0  
CMF C15 H22 O2



CM 3

CRN 868-77-9

L12 ANSWER 1 OF 1 CAPLUS COPYRIGHT 2005 ACS on STN  
 AN 2005:98956 CAPLUS  
 DN 142:207614  
 TI Photoresist polymer and photoresist composition containing the same  
 IN Lee, Geun Su; Bok, Cheol Kyu; Moon, Seung Chan; Shin, Ki Soo; Kim, Jae  
 Hyun; Kim, Jung Woo; Lee, Sang Hyang; Kang, Jae Hyun  
 PA S. Korea  
 SO U.S. Pat. Appl. Publ., 17 pp.  
 CODEN: USXXCO  
 DT Patent  
 LA English  
 FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI US 2005026070	A1	20050203	US 2003-719905	20031121
PRAI KR 2003-52337	A	20030729		

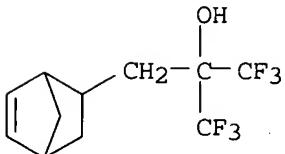
AB Photoresist polymers and photoresist compns. are disclosed. A photoresist polymer is represented by I ( $X_{1-4} = CH_2, CH_2CH_2, S; R_{1,2} = H, CH_3, CF_3; R_3 = C_{1-20}$  alkyl, etc.;  $R_4 = C_{1-20}$  hydroxyalkyl, etc.;  $R_5 = H, C_{1-20}$  hydroxyalkyl, etc.;  $m = 0-2$ ; and  $n = 0, 1$ ). The photoresist compns. have excellent etching resistance, thermal resistance and adhesive property, and high affinity to an developing solution, thereby improving LER (line edge roughness).

IT 836623-58-6P 836623-59-7P  
 RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)  
 (photoresist polymer for photoresist composition)

RN 836623-58-6 CAPLUS  
 CN 2-Propenoic acid, 2-methyl-, 2-hydroxyethyl ester, polymer with  $\alpha,\alpha$ -bis(trifluoromethyl)bicyclo[2.2.1]hept-5-ene-2-ethanol, 2,5-furandione and 2-methyltricyclo[3.3.1.13,7]dec-2-yl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

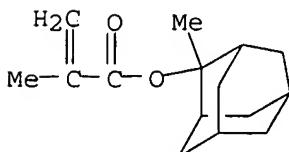
CM 1

CRN 196314-61-1  
 CMF C11 H12 F6 O



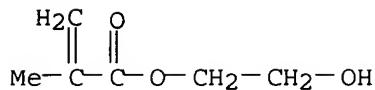
CM 2

CRN 177080-67-0  
 CMF C15 H22 O2



CM 3

CRN 868-77-9  
CMF C6 H10 O3



CM 4

CRN 108-31-6  
CMF C4 H2 O3

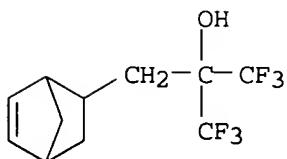


RN 836623-59-7 CAPLUS

CN 2-Propenoic acid, 2-methyl-, 2-hydroxyethyl ester, polymer with  
bicyclo[2.2.1]hept-2-ene,  $\alpha,\alpha$ -bis(trifluoromethyl)bicyclo[2.2.  
1]hept-5-ene-2-ethanol, 2,5-furandione and 2-methyltricyclo[3.3.1.13,7]dec-  
2-yl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

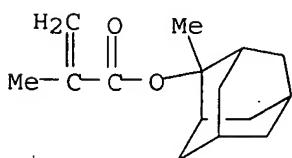
CM 1

CRN 196314-61-1  
CMF C11 H12 F6 O



CM 2

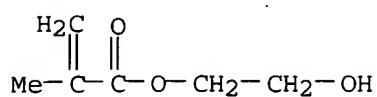
CRN 177080-67-0  
CMF C15 H22 O2



CM 3

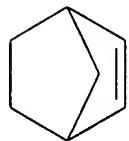
CRN 868-77-9

CMF C6 H10 O3



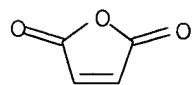
CM 4

CRN 498-66-8  
CMF C7 H10



CM 5

CRN 108-31-6  
CMF C4 H2 O3



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L16 ANSWER 1 OF 1 CAPLUS COPYRIGHT 2005 ACS on STN  
 AN 2005:98956 CAPLUS  
 DN 142:207614  
 TI Photoresist polymer and photoresist composition containing the same  
 IN Lee, Geun Su; Bok, Cheol Kyu; Moon, Seung Chan; Shin, Ki Soo; Kim, Jae  
 Hyun; Kim, Jung Woo; Lee, Sang Hyang; Kang, Jae Hyun  
 PA S. Korea  
 SO U.S. Pat. Appl. Publ., 17 pp.  
 CODEN: USXXCO  
 DT Patent  
 LA English  
 FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 2005026070	A1	20050203	US 2003-719905	20031121
PRAI	KR 2003-52337	A	20030729		

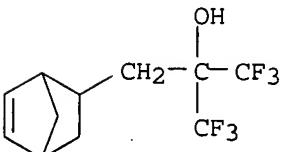
AB Photoresist polymers and photoresist compns. are disclosed. A photoresist polymer is represented by I ( $X1-4 = CH_2, CH_2CH_2, S; R1,2 = H, CH_3, CF_3; R3 = C1-20 alkyl, etc.; R4 = C1-20 hydroxyalkyl, etc.; R5 = H, C1-20 hydroxyalkyl, etc.; m = 0-2; and n = 0, 1$ ). The photoresist compns. have excellent etching resistance, thermal resistance and adhesive property, and high affinity to an developing solution, thereby improving LER (line edge roughness).

IT 836623-60-0P 836623-61-1P  
 RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)  
 (photoresist polymer for photoresist composition)

RN 836623-60-0 CAPLUS  
 CN 2-Propenoic acid, 2-methyl-, 1,1-dimethylethyl ester, polymer with  $\alpha,\alpha$ -bis(trifluoromethyl)bicyclo[2.2.1]hept-5-ene-2-ethanol, 2,5-furandione and 2-hydroxyethyl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

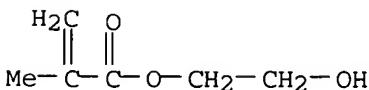
CM 1

CRN 196314-61-1  
 CMF C11 H12 F6 O



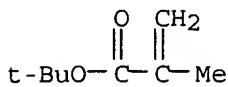
CM 2

CRN 868-77-9  
 CMF C6 H10 O3



CM 3

CRN 585-07-9  
CMF C8 H14 O2



CM 4

CRN 108-31-6  
CMF C4 H2 O3

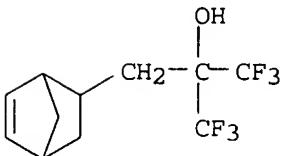


RN 836623-61-1 CAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylethyl ester,  
polymer with  $\alpha,\alpha$ -bis(trifluoromethyl)bicyclo[2.2.1]hept-5-ene-  
2-ethanol, 1,1-dimethylethyl 2-methyl-2-propenoate, 2,5-furandione and  
2-hydroxyethyl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

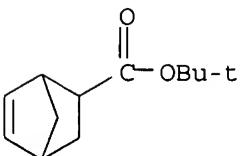
CM 1

CRN 196314-61-1  
CMF C11 H12 F6 O



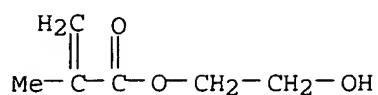
CM 2

CRN 154970-45-3  
CMF C12 H18 O2



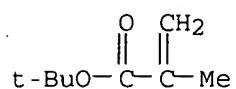
CM 3

CRN 868-77-9  
CMF C6 H10 O3



CM 4

CRN 585-07-9  
CMF C8 H14 O2



CM 5

CRN 108-31-6  
CMF C4 H2 O3



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